AP1608P1C-P22

1.6 x 0.8 mm Phototransistor



DESCRIPTION

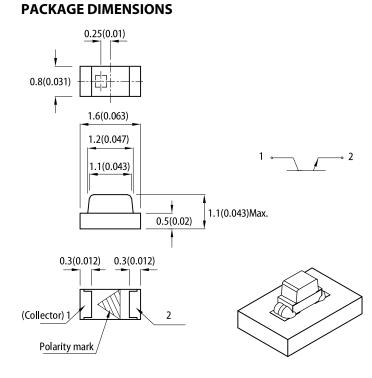
Made with silicon phototransistor chips

FEATURES

- 1.6 mm x 0.8 mm SMD LED, 1.1 mm thickness
- · Mechanically and spectrally matched to infrared emitting LED lamp
- Water clear lens
- Package: 2000 pcs / reel
- Moisture sensitivity level: 3
- Halogen-free
- · RoHS compliant

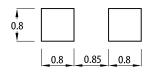
APPLICATIONS

- · Infrared applied systems
- Optoelectronic switches
- Photodetector control circuits
- Sensor technology



RECOMMENDED SOLDERING PATTERN

(units : mm; tolerance : ± 0.1)



Notes.

All dimensions are in millimeters (inches).
Tolerance is ±0.1(0.004") unless otherwise noted.

3. The specifications, characteristics and technical data described in the datasheet are subject to

The device has a single mounting surface. The device must be mounted according to the specifications.

ABSOLUTE MAXIMUM RATINGS at T_A=25°C

Parameter	Max.Ratings	Units
Collector-to-Emitter Voltage	30	V
Emitter-to-Collector Voltage	5	V
Power Dissipation at(or below) 25°C Free Air Temperature	100	mW
Operating Temperature	-40 to +85	°C
Storage Temperature	-40 to +85	°C

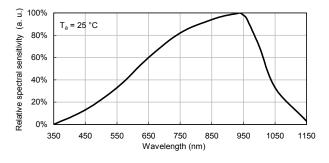
Note: 1. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

ELECTRICAL / OPTICAL CHARACTERISTICS at T_A = 25^{\circ}C

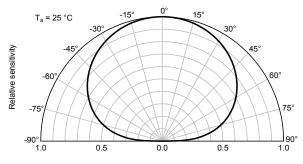
Parameter	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Collector-to-Emitter Breakdown Voltage	V _{BR CEO}	30	-	-	V	$I_{c} = 100\mu A$ $E_{e} = 0mW/cm^{2}$
Emitter-to-Collector Breakdown Voltage	V _{BR ECO}	5	-	-	V	I _E = 100μA E _e = 0mW/cm ²
Collector-to-Emitter Saturation Voltage	V _{CE (SAT)}	-	-	0.8	V	$I_{\rm C}$ = 2mA E _e = 20mW/cm ²
Collector Dark Current	I _{CEO}	-	-	100	nA	$V_{CE} = 10V$ $E_e = 0$ mW/cm ²
Rise Time(10% to 90%)	T _R	-	15	-	μS	V_{CE} = 5V I _C = 1mA R _L = 1000Ω
Fall Time(90% to 10%)	T _F	-	15	-	μS	
On State Collector Current	I _(ON)	0.1	0.3	-	mA	$V_{CE} = 5V$ $E_e = 1mW/cm^2$ $\lambda = 940nm$
Range of spectral bandwidth	λ _{0.1}	420	-	1120	nm	-
Wavelength of peak sensitivity	λ _p	-	940	-	nm	-
Angle of half sensitivity	201/2	-	150	-	deg	-

TECHNICAL DATA

RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH

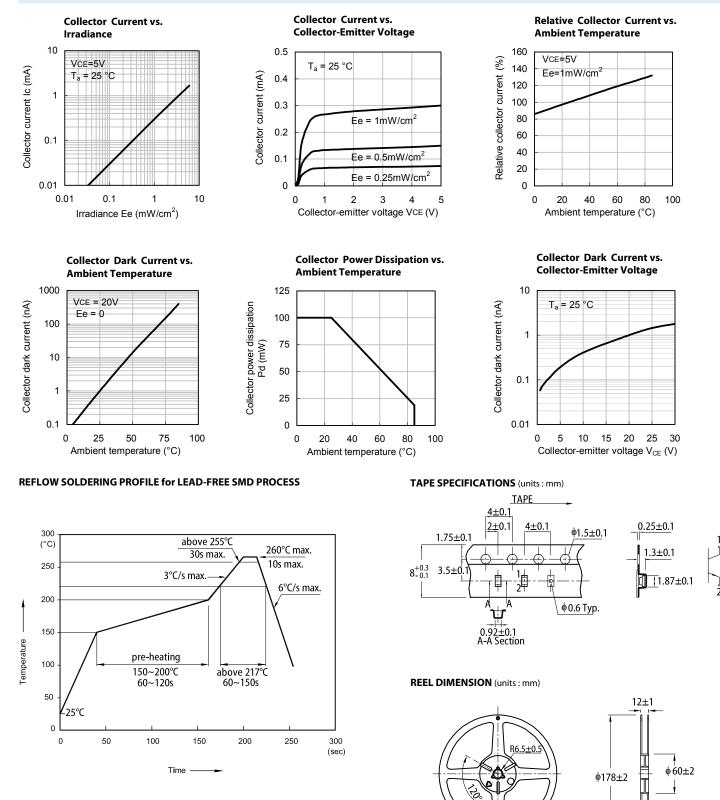


RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT



TECHNICAL DATA

PHOTOTRANSISTOR



Notes.

- 1. Don't cause stress to the LEDs while it is exposed to high temperature.

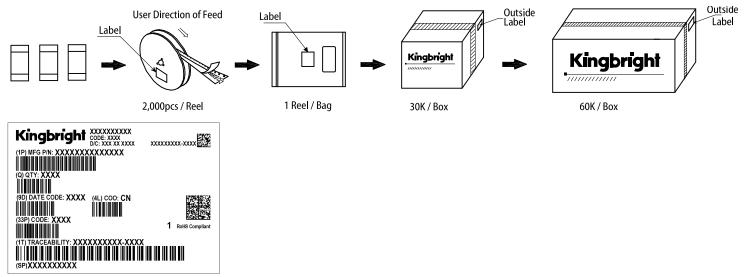
 The maximum number of reflow soldering passes is 2 times.
Reflow soldering is recommended. Other soldering methods are not recommended as they might cause damage to the product.

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9±1

AP1608P1C-P22

PACKING & LABEL SPECIFICATIONS



PRECAUTIONARY NOTES

- 1. 2.
- The information included in this document reflects representative usage scenarios and is intended for technical reference only. The part number, type, and specifications mentioned in this document are subject to future change and improvement without notice. Before production usage customer should refer to the latest datasheet for the updated specifications.
- 3. When using the products referenced in this document, please make sure the product is being operated within the environmental and electrical limits specified in the datasheet. If customer usage exceeds the specified limits. Kingbright will not be responsible for any subsequent issues. The information in this document applies to typical usage in consumer electronics applications. If customer's application has special reliability requirements or have life-threatening
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- 5.
- 6. Notes